

Fig.1A
Related Art

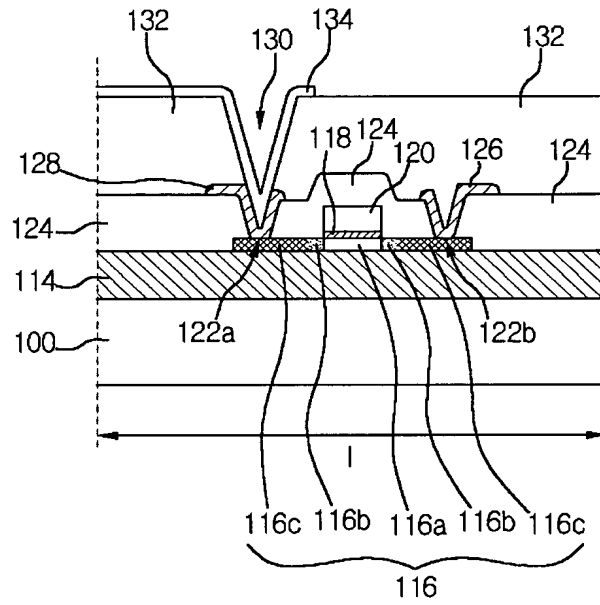


Fig.1B
Related Art

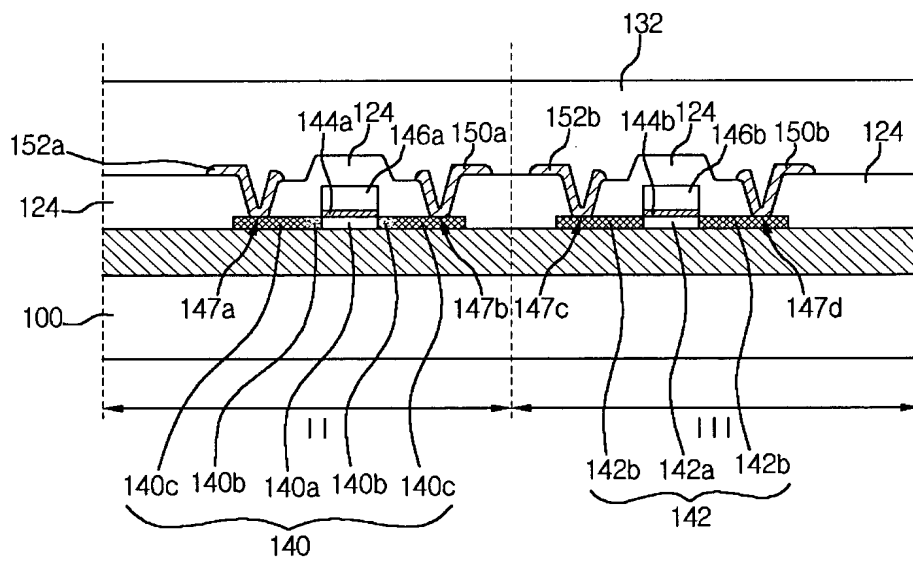
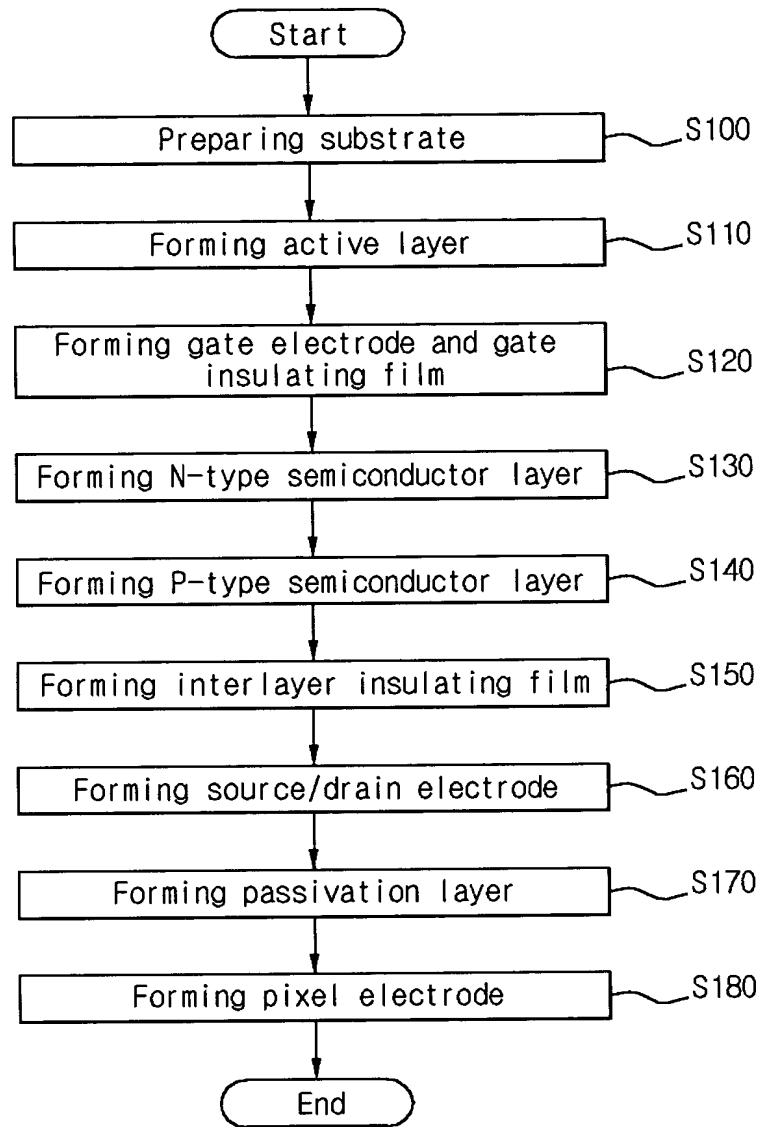


Fig.2
Related Art



3

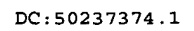


Fig. 10 is a cross-sectional view of a semiconductor device. It shows a substrate 200 with a layer 214 on top. A central structure 218 is surrounded by a layer 220. A layer 224 is on the left. A group of five curved lines 216a, 216b, 216b, 216b, 216c are shown, with a bracket 216 underneath them. A label IV is on the right.

[illegible]

[illegible][illegible]

Fig.5

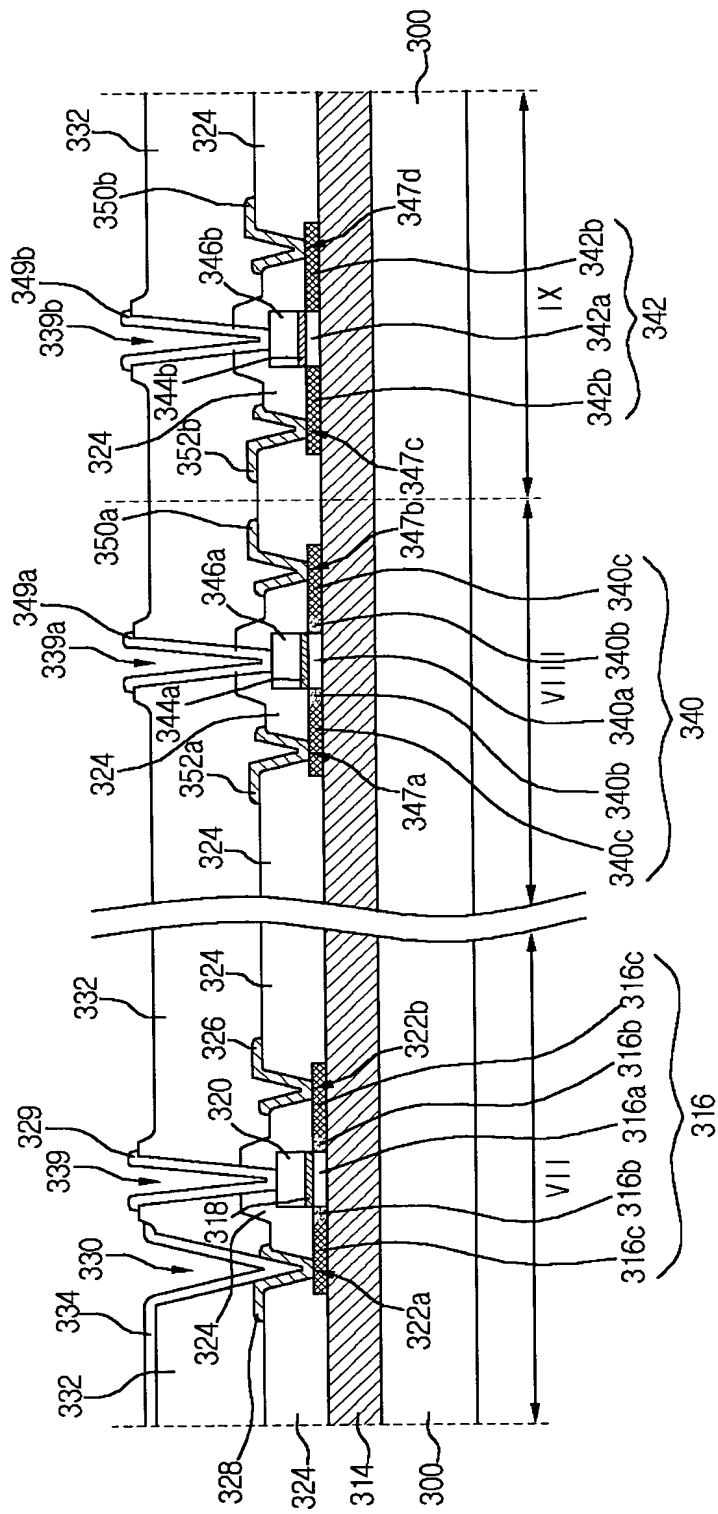


Fig.6A

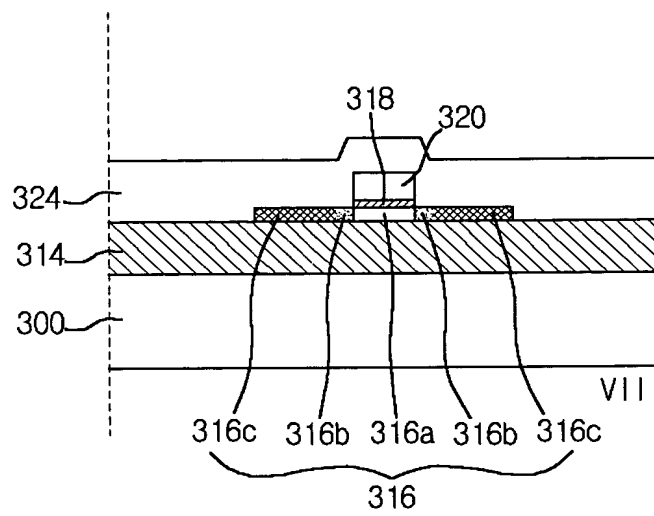


Fig.6B

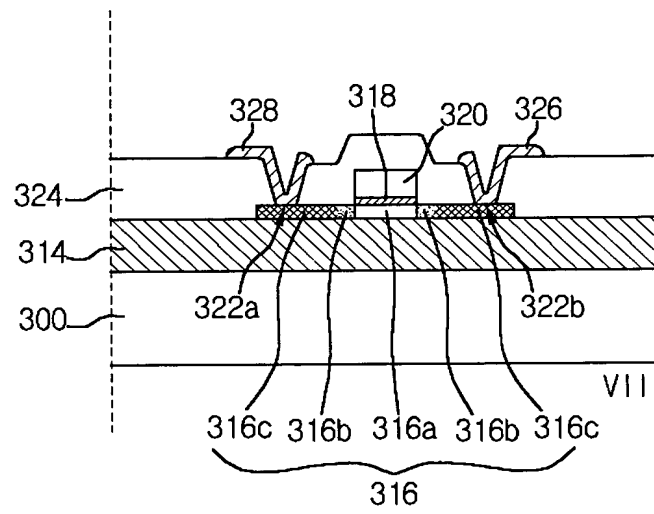


Fig.6C

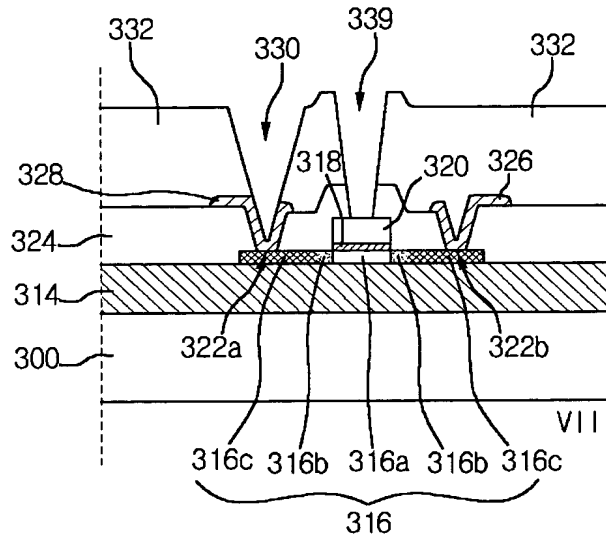


Fig.6D

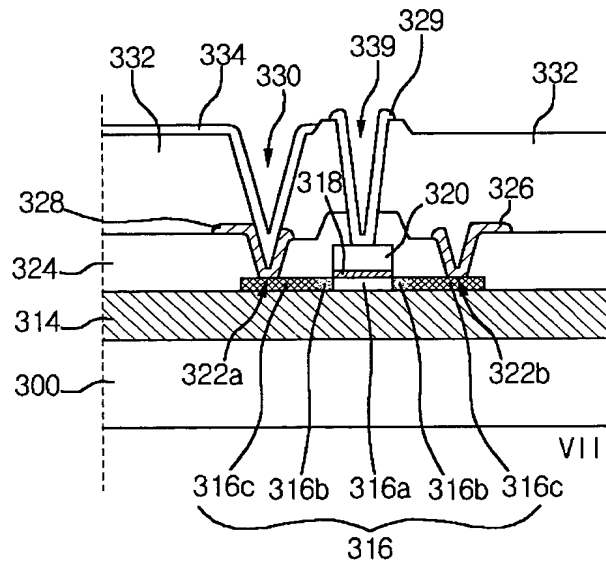


Fig.7

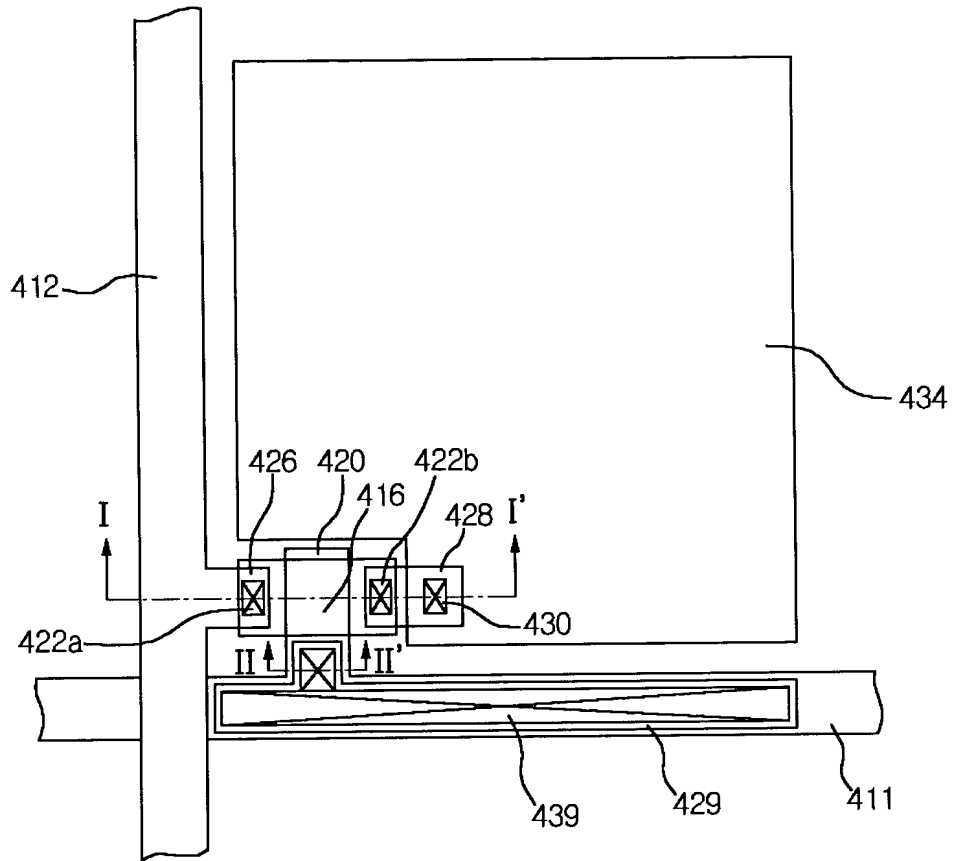


Fig.8A

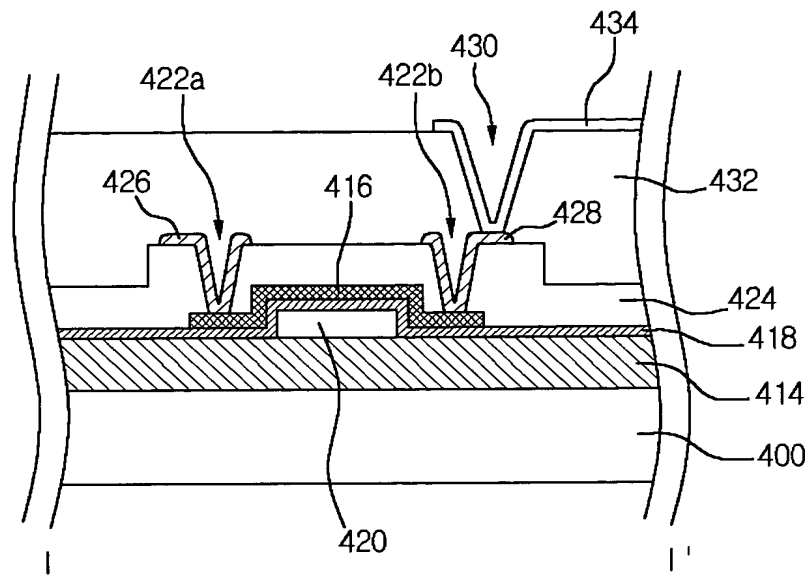


Fig.8B

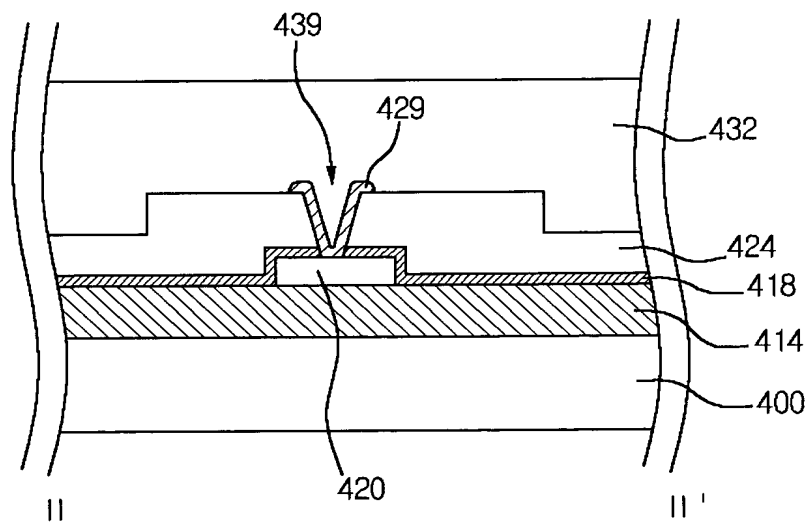


Fig.9

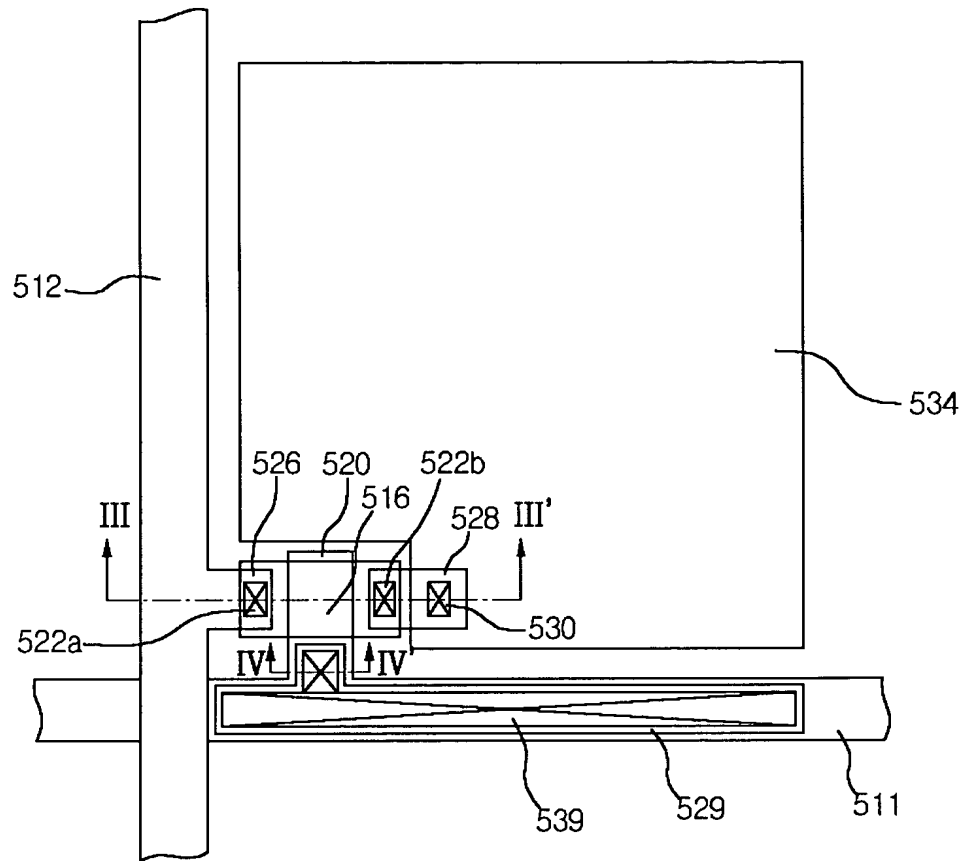


Fig.10A

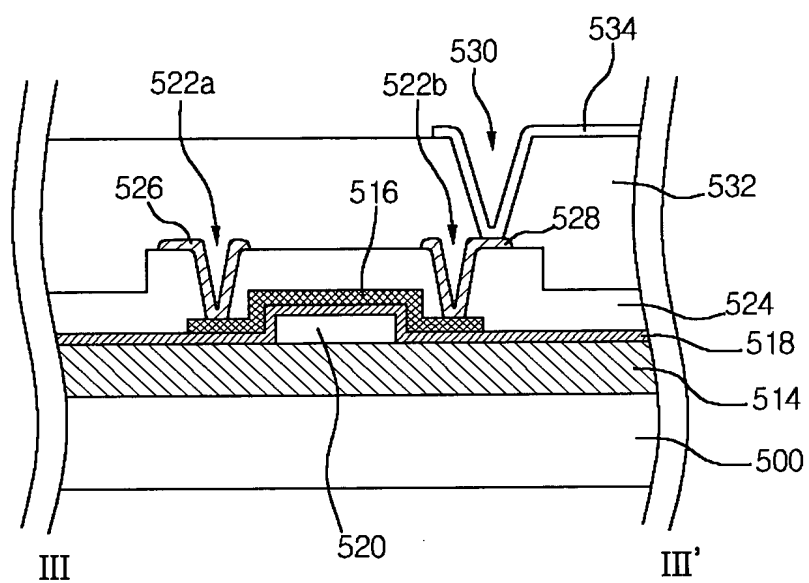


Fig.10B

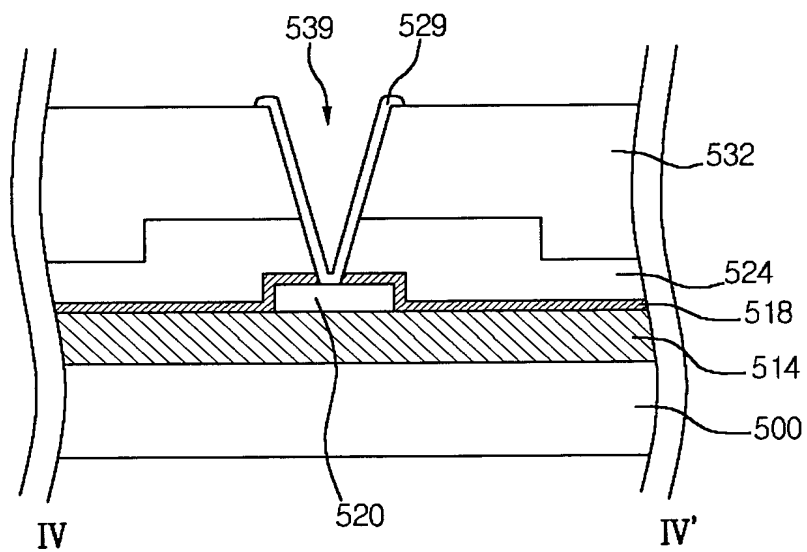


Fig.11A

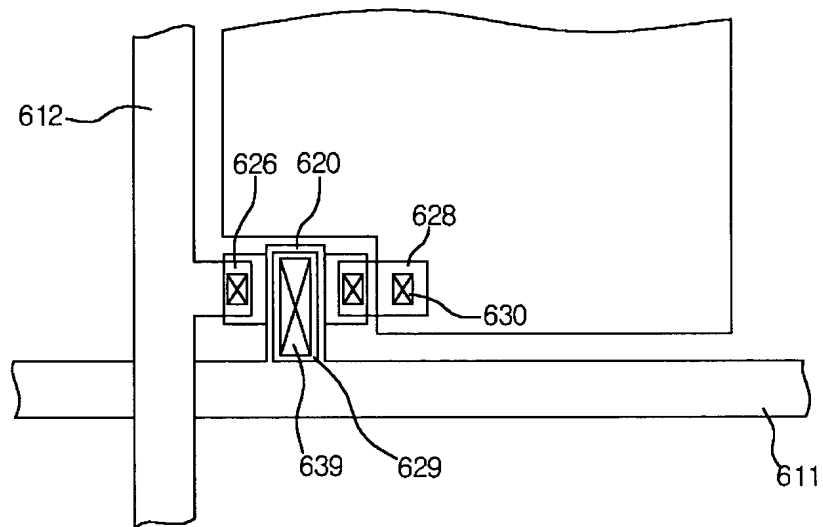


Fig.11B

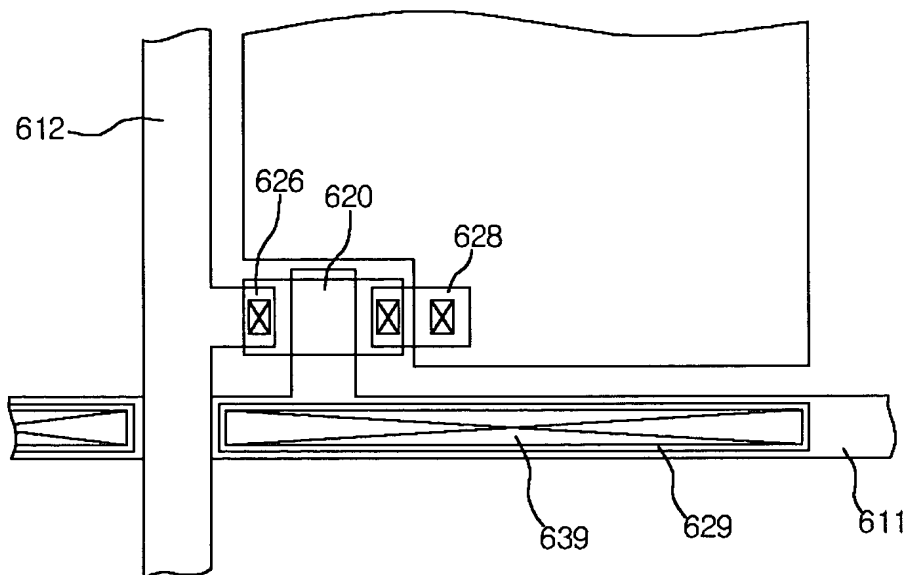


Fig.11C

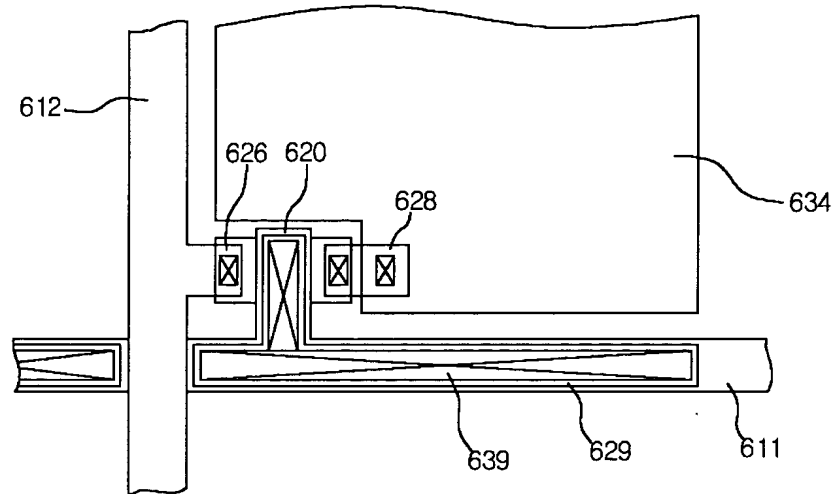


Fig.11D

